Amendments to the Claims:

This listing of the claims will replace all prior versions, and listings of claims in the application.

Listings of Claims:

1. (Currently Amended) A magnetic sensing element comprising a multilayer film including a first antiferromagnetic layer, a pinned magnetic layer, a non-magnetic material layer and a free magnetic layer in that order from the bottom,

wherein the free magnetic layer comprises a first free magnetic layer having a predetermined dimension in a track-width direction and a second free magnetic layer which is provided on the first free magnetic layer and which has a dimension in the track-width direction larger than that of the first free magnetic layer, a second antiferromagnetic layer for aligning a magnetization direction of the free magnetic layer in one direction is provided as a layer above the second free magnetic layer, and a pair of electrode layers are is provided on both side portions of the multilayer film along the track-width direction.

- 2. (Original) The magnetic sensing element according to Claim 1, wherein the first free magnetic layer and the second free magnetic layer are provided as an integrated ferromagnetic layer.
- 3. (Original) The magnetic sensing element according to Claim 1, wherein a non-magnetic intermediate layer is provided between the first free magnetic layer and the second free magnetic layer.
- 4. (Previously Presented) The magnetic sensing element according to Claim 3, wherein the non-magnetic intermediate layer comprises at least one of Ru, Re, Pd, Os, Ir, Cr, Pt, Au, Cu and Rh.
- 5. (Original) The magnetic sensing element according to Claim 4, wherein the non-magnetic intermediate layer comprises Cu.

- 6. (Original) The magnetic sensing element according to Claim 1, wherein the dimension in the track-width direction of the first free magnetic layer is 0.18 μm or less.
- 7. (Original) The magnetic sensing element according to Claim 6, wherein the dimension in the track-width direction of the first free magnetic layer is 0.15 μm or less.
- 8. (Currently Amended) The magnetic sensing element according to Claim 1, wherein [(a difference calculated by subtracting a film thickness, along the height of the multilayer film, of the free magnetic layer in a track-width region from a film thickness, along the height of the multilayer film, of the free magnetic layer in both side regions of the track-width region) / the film thickness of the free magnetic layer in the track-width region] × 100 (%) is within the range of -80% or more, but less than 0%.
- 9. (Currently Amended) The magnetic sensing element according to Claim 1, wherein a film thickness, along the height of the multilayer film, of the second free magnetic layer in both side regions of a track-width region is 10 angstroms or more, but 50 angstroms or less.
- 10. (Currently Amended) The magnetic sensing element according to Claim 1, wherein a film thickness, along the height of the multilayer film, of the free magnetic layer in a track-width region is 30 angstroms or more, but 50 angstroms or less.
- 11. (Currently Amended) The magnetic sensing element according to Claim 1, wherein the second antiferromagnetic layer is laminated on a track-width region of the second free magnetic layer as well, and a film thickness, along the height of the multilayer film, of the second antiferromagnetic layer on the track-width region is smaller than a thickness of the second antiferromagnetic layer, along the height of the multilayer film, in both side regions located on both sides thereof.

- 12. (Original) The magnetic sensing element according to Claim 11, wherein the second antiferromagnetic layer provided on the track-width region of the second free magnetic layer has a non-antiferromagnetic property, and both the side regions of the second antiferromagnetic layer have an antiferromagnetic property.
- 13. (Currently Amended) The magnetic sensing element according to Claim 11, wherein one of the second antiferromagnetic layer is provided on the track-width region of the second free magnetic layer so as to have a film thickness, along the height of the multilayer film, of 50 angstroms or less, and no antiferromagnetic layer is provided on the track-width region of the free magnetic layer.

14. (Cancelled)

- 15. (Previously Presented) The magnetic sensing element according to Claim 11, wherein a spacing in the track-width direction between inner end surfaces of both the side regions of the second antiferromagnetic layer is larger than the dimension in the track-width direction of the first free magnetic layer.
- 16. (Original) The magnetic sensing element according to Claim 11, wherein the second antiferromagnetic layer is directly laminated on the second free magnetic layer.
- 17. (Original) The magnetic sensing element according to Claim 16, wherein successive film formation of the second antiferromagnetic layer is performed on the second free magnetic layer.
- 18. (Currently Amended) The magnetic sensing element according to Claim 1, wherein a pairboth side regions of the second antiferromagnetic layers, having a spacing therebetween along the track width direction, are provided on the second free magnetic layer, with a third antiferromagnetic layer provided therebetween the second antiferromagnetic layer and the second free magnetic layer.

- 19. (Currently Amended) The magnetic sensing element according to Claim 18, wherein a non-magnetic intermediate layer is laminated between the third antiferromagnetic layer and both side regions of the second antiferromagnetic layer.
- 20. (Previously Presented) The magnetic sensing element according to Claim 18, wherein a central portion of the third antiferromagnetic layer has a non-antiferromagnetic property, and both side regions of the third antiferromagnetic layer have an antiferromagnetic property.
- 21. (Currently Amended) The magnetic sensing element according to Claim 18, wherein a film thickness, along the height of the magnetic film, of the third antiferromagnetic layer is 5 angstroms or more, but 50 angstroms or less.
- 22. (Original) The magnetic sensing element according to Claim 18, wherein successive film formation of the third antiferromagnetic layer is performed on the second free magnetic layer.
- 23. (Original) The magnetic sensing element according to Claim 1, wherein a pair of the second antiferromagnetic layers having a spacing in the track-width direction are provided on the second free magnetic layer through a pair of ferromagnetic layers provided so as to have a spacing in the track-width direction.
- 24. (Original) The magnetic sensing element according to Claim 23, wherein successive film formation of the second antiferromagnetic layers is performed on the ferromagnetic layers.
- 25. (Previously Presented) The magnetic sensing element according to Claim 23, wherein a total film thickness of a film thickness of the ferromagnetic layer and a film thickness of the second free magnetic layer is smaller than a total film thickness of the film thickness of the first free magnetic layer and a film thickness of the second free magnetic layer.

- 26. (Original) The magnetic sensing element according to Claim 23, wherein a non-magnetic intermediate layer is laminated between the second free magnetic layer and the ferromagnetic layer.
- 27. (Original) The magnetic sensing element according to Claim 26, wherein the non-magnetic intermediate layer comprises at least one noble metal of Ru, Re, Pd, Os, Ir, Pt, Au, Rh and Cu.
- 28. (Original) The magnetic sensing element according to Claim 26, wherein the non-magnetic intermediate layer comprises Cr.
 - 29. (Cancelled)
- 30. (Original) The magnetic sensing element according to Claim 23, wherein3the spacing in the track-width direction between the pair of second antiferromagnetic layers is larger than the dimension in the track-width direction of the first free magnetic layer.

31 - 48. (Cancelled)